

FEATURES

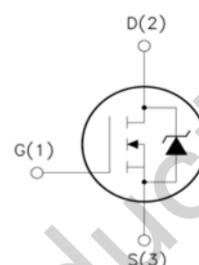
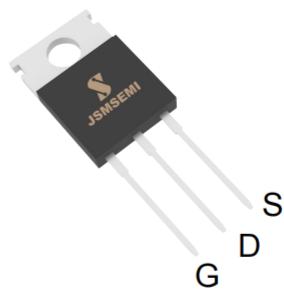
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information

Device	Package	Marking
MTP50N05EL	TO-220	MTP50N05EL



- 1.Gate (G)
- 2.Drain (D)
- 3.Source (S)

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-220	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	60	V
Continuous Drain Current	I_D	110	A
Pulsed Drain Current (note1)	I_{DM}	440	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	653	mJ
Avalanche Current (note1)	I_{AS}	40	A
Repetitive Avalanche Energy (note1)	E_{AR}	391.8	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	358	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.65	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	60	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 60\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 60\text{A}$	--	0.005	0.006	Ω
Forward Transconductance	g_{fs}	$V_{\text{DS}} = 25\text{V}, I_D = 60\text{A}$	--	17	--	S
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	2699	--	pF
Output Capacitance	C_{oss}		--	1016	--	
Reverse Transfer Capacitance	C_{rss}		--	487	--	
Total Gate Charge	Q_g	$V_{\text{DS}}=28\text{V}, V_{\text{GS}} = 15\text{V}, I_D=42\text{A}$	--	115	--	nC
Gate-Source Charge	Q_{gs}		--	13	--	
Gate-Drain Charge	Q_{gd}		--	55	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 28\text{V}, I_D = 42\text{A}, V_{\text{GS}} = 15\text{V}.RG = 25\Omega$	--	52	--	ns
Turn-on Rise Time	t_r		--	142	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	355	--	
Turn-off Fall Time	t_f		--	230	--	
Drain-Source Body Diode Characteristics						
Continuous Source Current	I_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 60\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	110	A
Pulsed Source Current	I_{SM}		--	--	440	
Body Forward Voltage	V_{SD}	$I_S = 40\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.2	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}} = 0\text{V}, I_F = 180\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	--	100	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.33	--	μC

Notes

- Repetitive Rating: Pulse width limited by maximum junction temperature
- $L=1\text{mH}, V_{\text{DD}} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

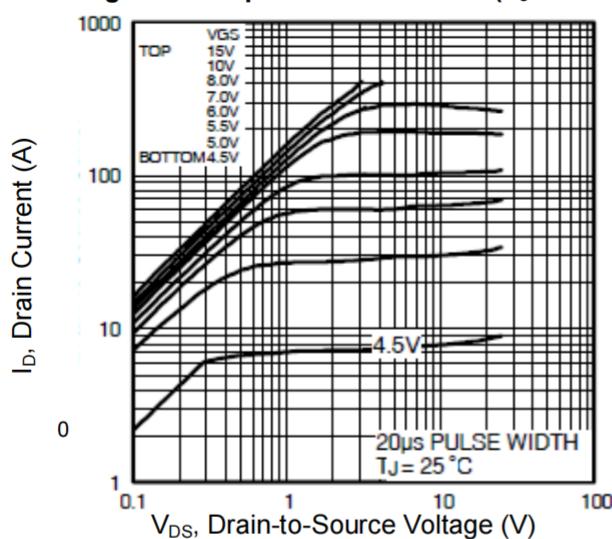


Figure 2. Body Diode Forward Voltage

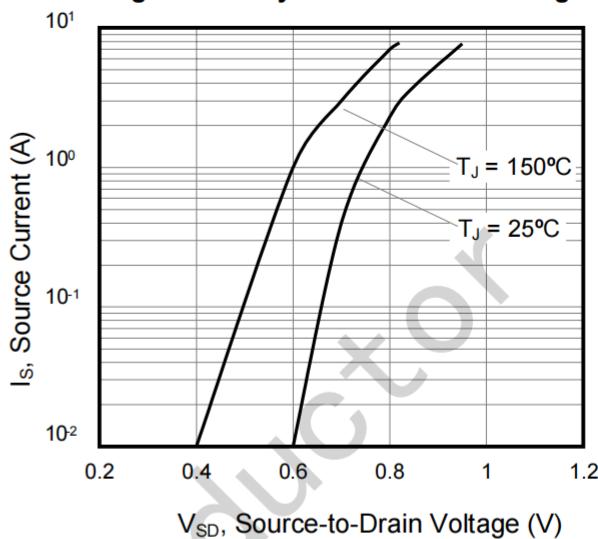


Figure 3. Drain Current vs. Temperature

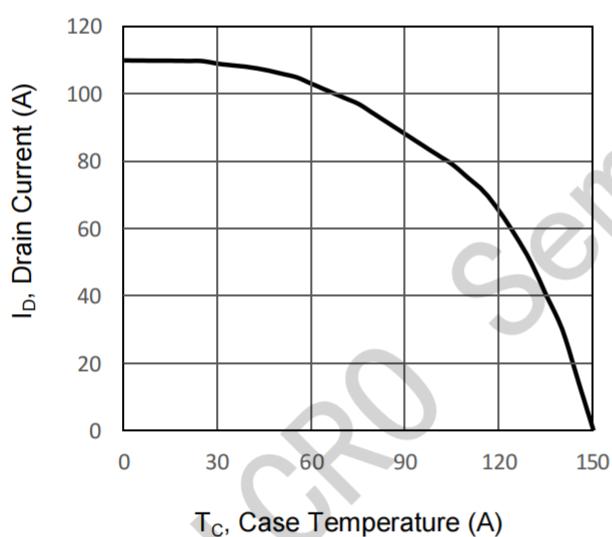


Figure 4. BV_{DSS} Variation vs. Temperature

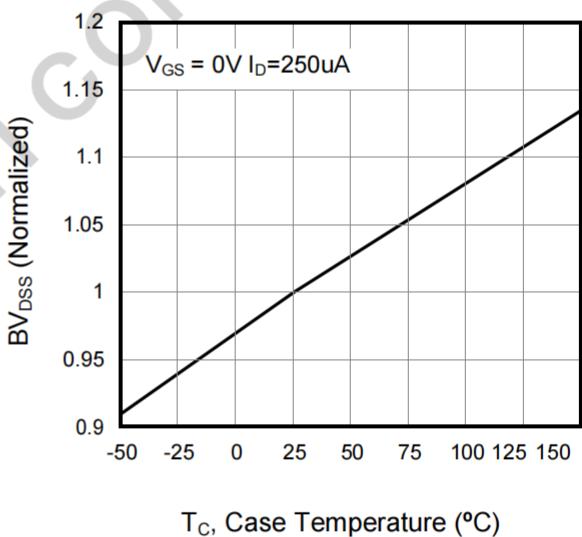


Figure 5. Transfer Characteristics

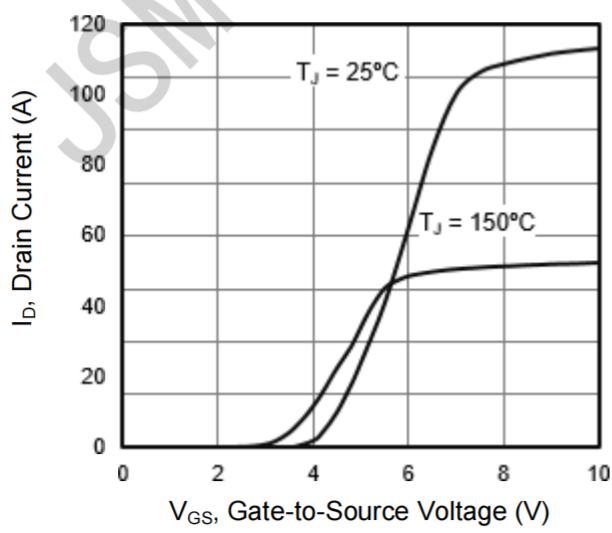
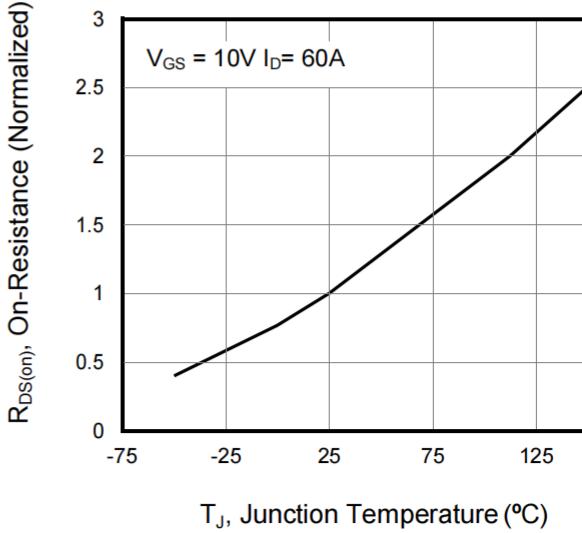


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

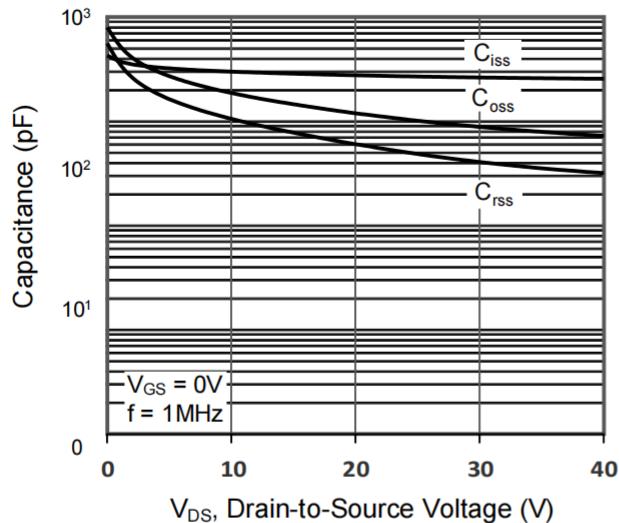


Figure 8. Gate Charge

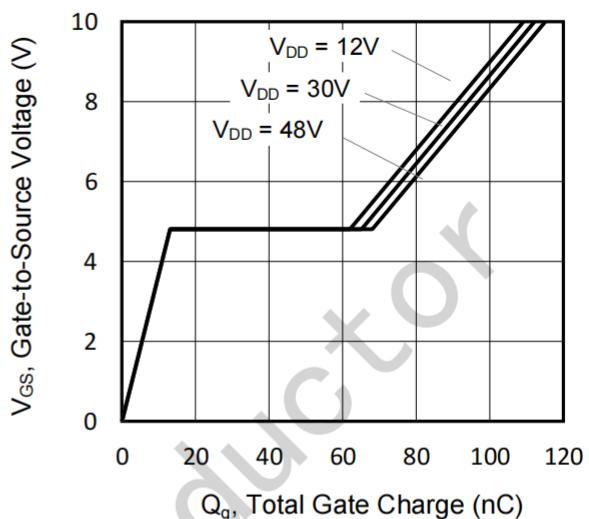


Figure 9. Transient Thermal Impedance
TO-220

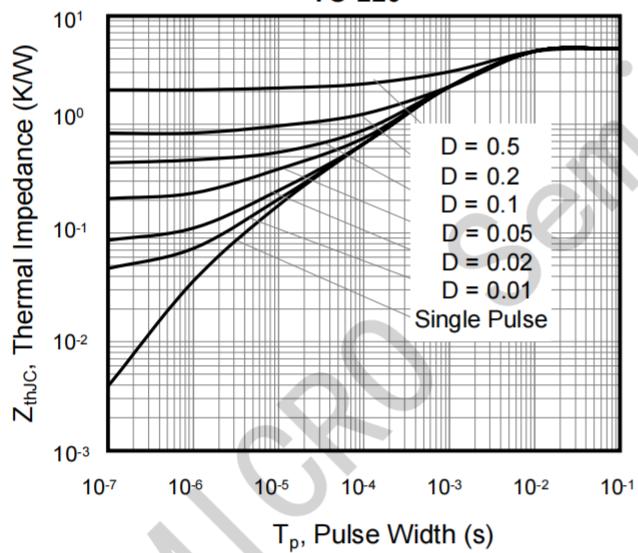
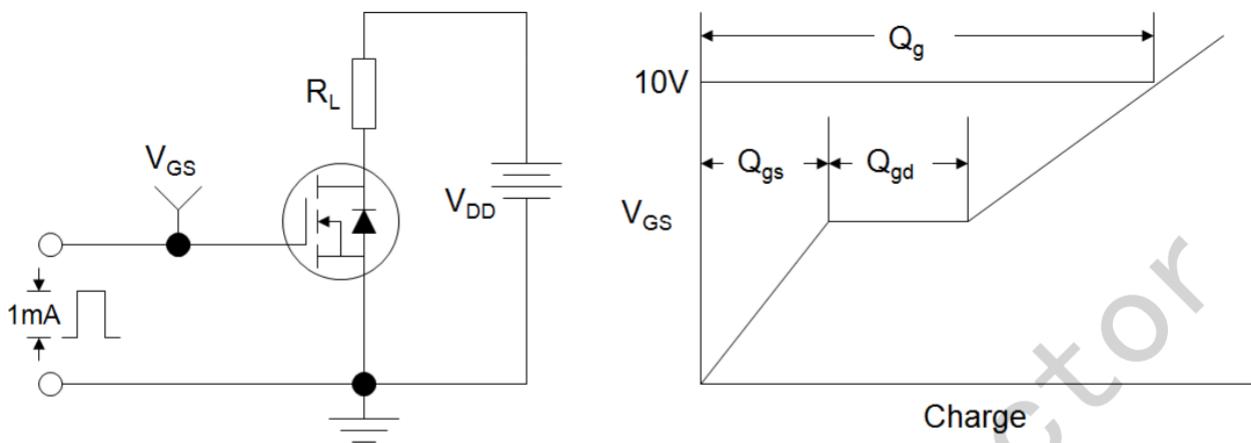
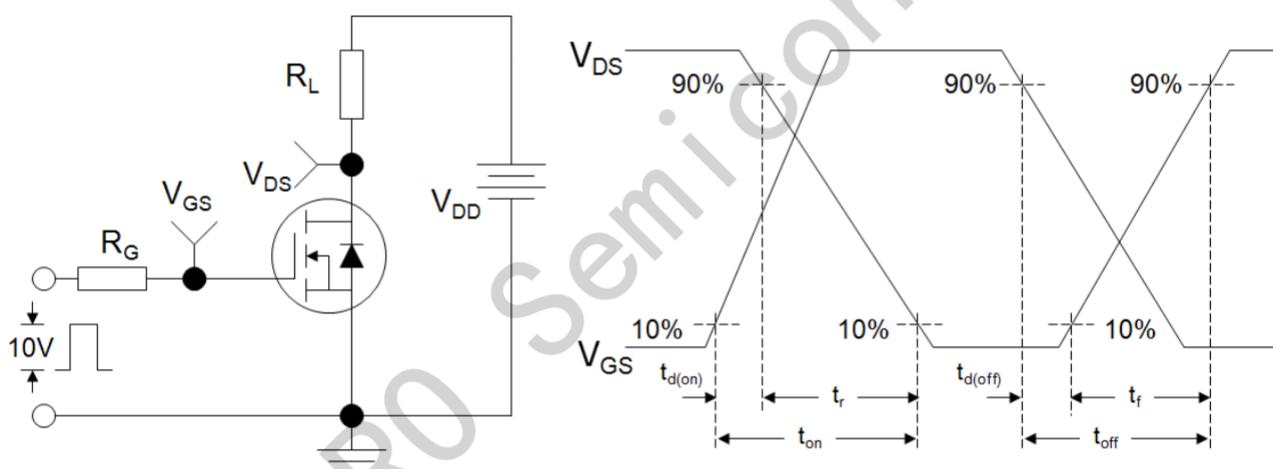
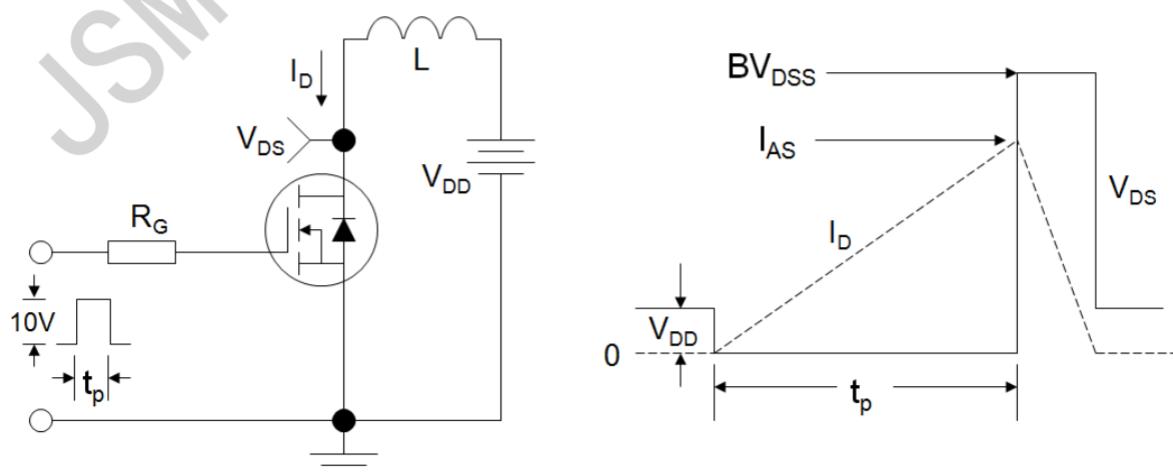
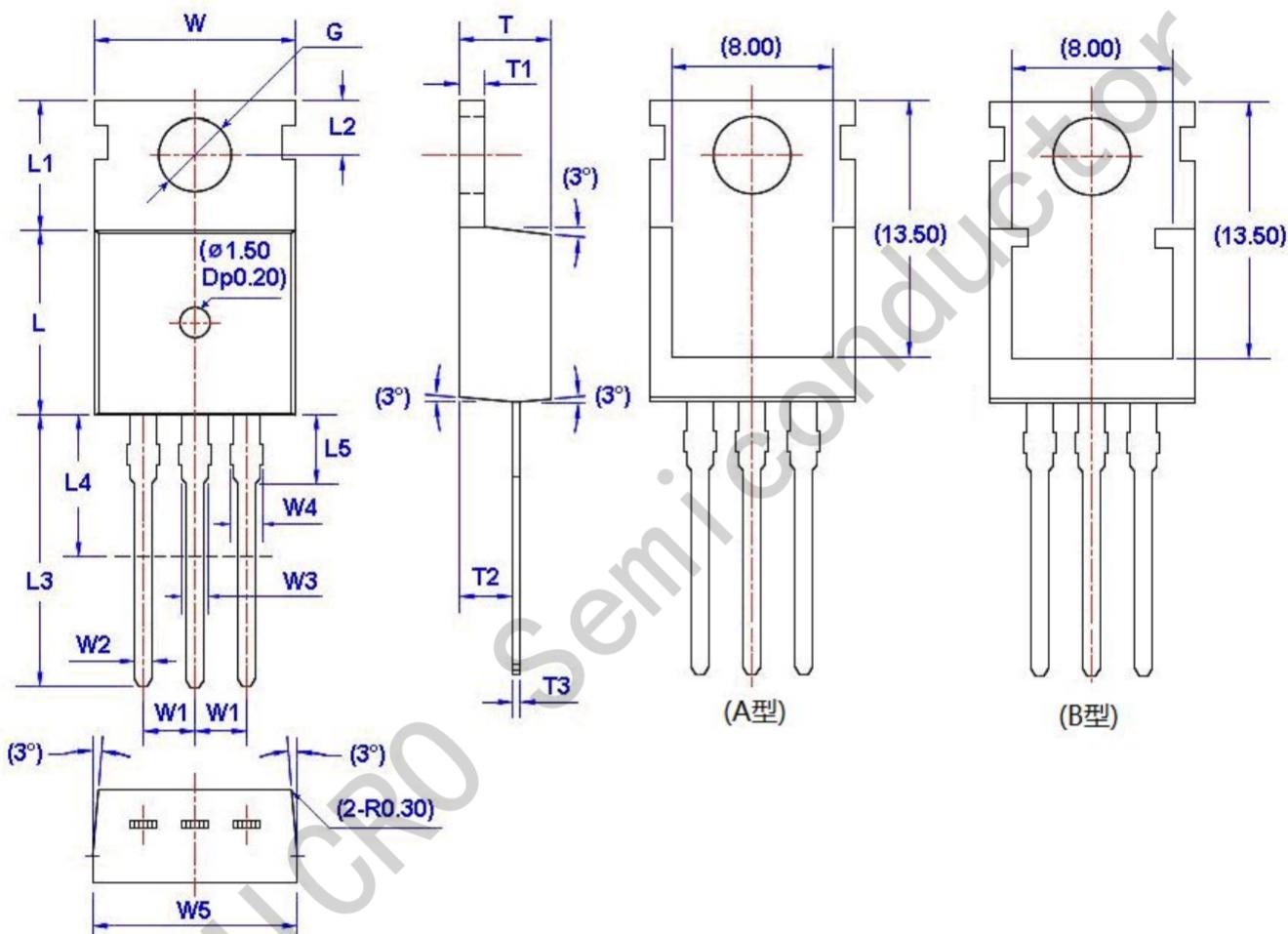


Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


Package Information

TO-220



Unit: mm

Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.66	10.28	W5	9.80	10.20	L4**	6.20	6.60	T3	0.45	0.60
W1	2.54 (TYP)		L	9.00	9.40	L5	2.79	3.30	G(Φ)	3.50	3.70
W2	0.70	0.95	L1	6.40	6.80	T	4.30	4.70			
W3	1.17	1.37	L2	2.70	2.90	T1	1.15	1.40			
W4*	1.32	1.72	L3	12.70	14.27	T2	2.20	2.60			

单击下面可查看定价，库存，交付和生命周期等信息

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